



COMPLEX ARRAY FOR RELAY DRIVERS

Features and Benefits

- Epitaxial Planar Die Construction
- One Transistor and One Switching Diode in One Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Alloy 42 lead-frame.
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (approximate)







DRDP006W



DRDNB16W

ПП

R1 = 1K Ω R2 = 10K Ω

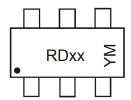
Ordering Information (Note 4)

Device	Compliance	Packaging	Shipping
DRDP006W-7	Commercial	SOT-363	3000/Tape & Reel
DRDNB16W-7	Commercial	SOT-363	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



RDxx = Product Type Marking Code: RD02 = DRDP006W RD03 = DRDNB16W YM = Date Code Marking Y = Year (ex: I = 2021) M = Month (ex: 9 = September)

Date Code Kev

Year	2005			2021		2022	2023		2024	2025		2026
Code	S			I		J	K		L	М		N
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings, Total Device @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_{D}	200	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	$R_{ hetaJA}$	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Maximum Ratings, DRDP006W PNP Transistor @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current (Note 5)	Ic	-600	mA

Maximum Ratings, DRDNB16W Pre-Biased NPN Transistor @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V _{CC}	50	V
Input Voltage	V _{IN}	-5 to +10	V
Output Current	lc	600	mA

Maximum Ratings, Switching Diode @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	75	V
RMS Reverse Voltage	V _{R(RMS)}	53	V
Forward Continuous Current (Note 5)	I _{FM}	500	mA
Average Rectified Output Current (Note 5)	I _O	250	mA
Non-Repetitive Peak Forward Surge Current @ t = 1.0μs @ t = 1.0s	I _{FSM}	4.0 1.0	А

Note: 5. Device mounted on FR-4 PCB, 1 inch square 2oz copper pad area.



Electrical Characteristics, DRDP006W PNP Transistor @TA = 25°C unless otherwise specified

Characteristic (Note 6)	Symbol	Min	Тур	Max	Unit	Test Condition
DC Current Gain	h _{FE}	_	100	300	_	I _C = -150mA, V _{CE} = -10V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	_	-0.4	V	I _C = -150mA, I _B = -15mA
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-60	_	_	V	$I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-60	_	_	V	$I_C = -10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5	_	_	V	$I_E = -10\mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_	_	-10	nA	V _{CB} = -50V, I _E = 0
Current Gain-Bandwidth Product	f _T	_	200	_	MHz	V _{CE} = -20V, I _C = -50mA, f = 100MHz
Capacitance	C _{obo}	_	_	8	pF	V _{CB} = -10V, I _E = 0, f = 1MHz

Electrical Characteristics, DRDNB16W Pre-Biased NPN Transistor @TA = 25°C unless otherwise specified

Characteristic (Note 6)	Symbol	Min	Тур	Max	Unit	Test Condition
Input Voltage	V _{I(off)}	0.3			>	V _{CC} = 5V, I _O = 100μA
Imput voitage	V _{I(on)}	_	_	2.0	V	V _O = 0.3V, I _O = 20mA
Output Voltage	V _{O(on)}	_	_	0.3	V	I _O /I _I = 50mA/2.5mA
Input Current	l _l	_	_	7.2	mA	V _I = 5V
Output Current	I _{O(off)}	_	_	0.5	μA	V _{CC} = 50V, V _I = 0V
DC Current Gain	Gı	56	_	_	_	V _O = 5V, I _O = 50mA
Gain-Bandwidth Product	f _T	_	200		MHz	V _{CE} = 10V, I _E = 5mA, f = 100MHz

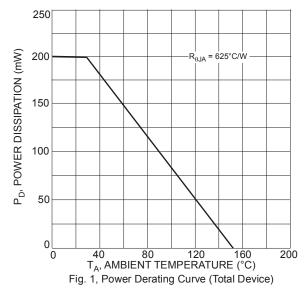
Electrical Characteristics, Switching Diode @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
Reverse Breakdown Voltage (Note 6)	$V_{(BR)R}$	75	_		$I_R = 10\mu A$
Forward Voltage	V _F	0.62 — — —	0.72 0.855 1.0 1.25	٧	I _F = 5.0mA I _F = 10mA I _F = 100mA I _F = 150mA
Reverse Current (Note 6)	I _R	_	2.5 50 30 25	μΑ μΑ μΑ nA	$V_R = 75V$ $V_R = 75V$, $T_J = 150$ °C $V_R = 25V$, $T_J = 150$ °C $V_R = 20V$
Total Capacitance	Ст	_	4.0	pF	V _R = 0, f = 1.0MHz
Reverse Recovery Time	t _{rr}	_	4.0	ns	$I_F = I_R = 10 \text{mA},$ $I_{rr} = 0.1 \times I_R, R_L = 100 \Omega$

Note: 6. Short duration pulse test used to minimize self-heating effect.



Device Characteristics



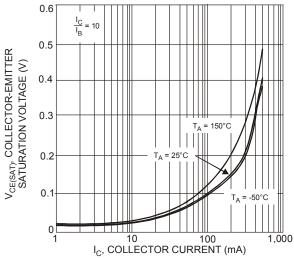
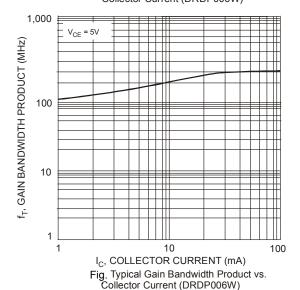
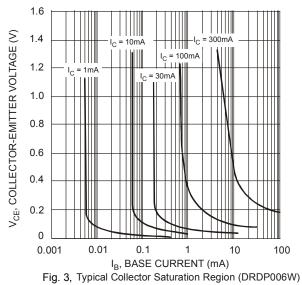


Fig. 2, Typical Collector-Emitter Saturation Voltage vs. Collector Current (DRDP006W)





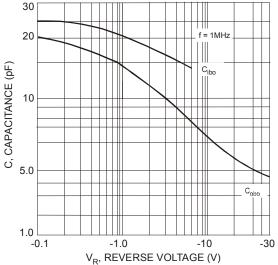


Fig. 5, Typical Capacitance (DRDP006W)



Device Characteristics (continued)

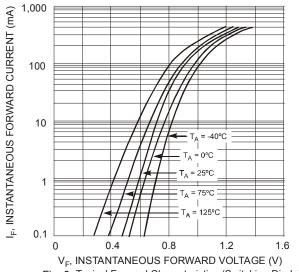


Fig. 6, Typical Forward Characteristics (Switching Diode)

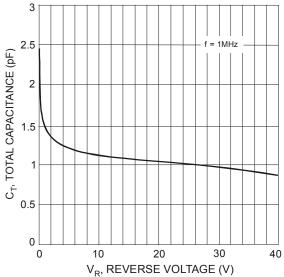


Fig. 8, Typical Capacitance vs. Reverse Voltage (Switching Diode)

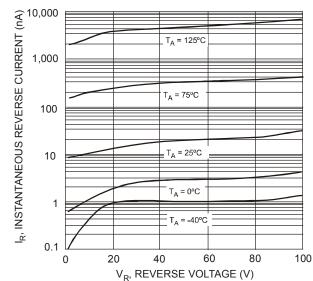
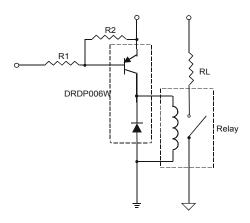


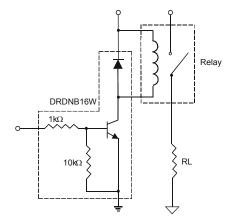
Fig. 7, Typical Reverse Characteristics (Switching Diode)



Sample Applications



Application Example: DRDP006W current source configuration, bias resistors not included



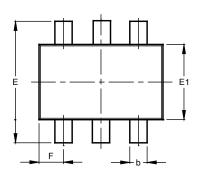
Application Example: DRDNB16W current sink configuration with built-in bias resistors

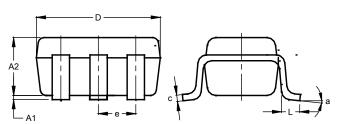


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



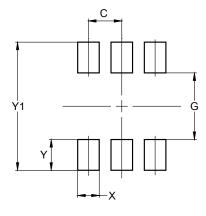


SOT363						
Dim	Min	Max	Тур			
A1	0.00	0.10	0.05			
A2	0.90	1.00	0.95			
b	0.10	0.30	0.25			
C	0.10	0.22	0.11			
D	1.80	2.20	2.15			
Е	2.00	2.20	2.10			
E1	1.15	1.35	1.30			
е	C	.650 E	SC			
F	0.40	0.45	0.425			
L	0.25	0.40	0.30			
а	0°	8°				
All I	Dimen	sions	in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT363



Dimensions	Value
Dillielisiolis	(in mm)
С	0.650
G	1.300
Х	0.420
Υ	0.600
Y1	2.500



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